Rev.2.0 Aug.29 2024

JSKT136&JSKH136

Description

1) A package of series of two chips.
2) With high thermal conductivity DBC as the insulation.
3) Welding by vacuum welding technology, which provide high reliability.

Typical Application

DC motor control, temperature control and light control system.

Absolute Maximum Ratings (Packaged into modules, unless otherwise specified, T_{CASE}=25)

Parameter	**Test Conditions**	**Symbol**	**Values**		**Unit**
			20	22	
Operating junction temperature range		T_j	-40~125		
Storage temperature range		T_{stg}	-40~125		
Repetitive peak off-state voltage	T_j=25	V_{DRM}	2000	2200	V
Repetitive peak reverse voltage	T_j=25	V_{RRM}	2000	2200	V

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		$_{T(AV)}$/$I_{F(AV)}$	130	A
Peak on-state surge current	t_P=10ms V_R=0.6V_{RRM}	I_{TSM}/I_{FSM}	2600	A
I^2t value for fusing	t_P=10ms V_R=0.6V_{RRM}	I^2t	33800	A^2s
Critical rate of rise of on-state current	I_G=2×I_{GT}	dI/dt	150	A/μs
Insulation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V

Electrical Characteristics (Packaged into modules, unless otherwise specified, T_{CASE}=25)

Parameter	**Test Conditions**	**Symbol**	**Values**	**Unit**
Peak on-state voltage	I_T=390A t_P=380μs	V_{TM}	≤1.8	V

Threshold voltage T_j=125

Repetitive peak reverse current	$V_R=V_{RRM}$ $T_C=25$ $T_C=125$	I_{RRM1} I_{RRM2}	≤100 ≤50	μA mA
Triggering gate current	$V_D=12V$ $R_L=30\Omega$	I_{GT}	20-120	mA
Holding current	$I_T=1A$	I_H	≤250	mA
Latching current	$I_G=1.2\ I_{GT}$	I_L	≤300A	

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FIG.3: Forward characteristics
(per thyristor or diode)